

**Silicon NPN Power Transistors**

**2N5239**

**DESCRIPTION**

- With TO-3 package
- High breakdown voltage
- High power dissipation

**APPLICATIONS**

- Switching regulator
- Inverters
- Power amplifiers
- Deflection circuits
- High-voltage bridge amplifiers

**PINNING (See Fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

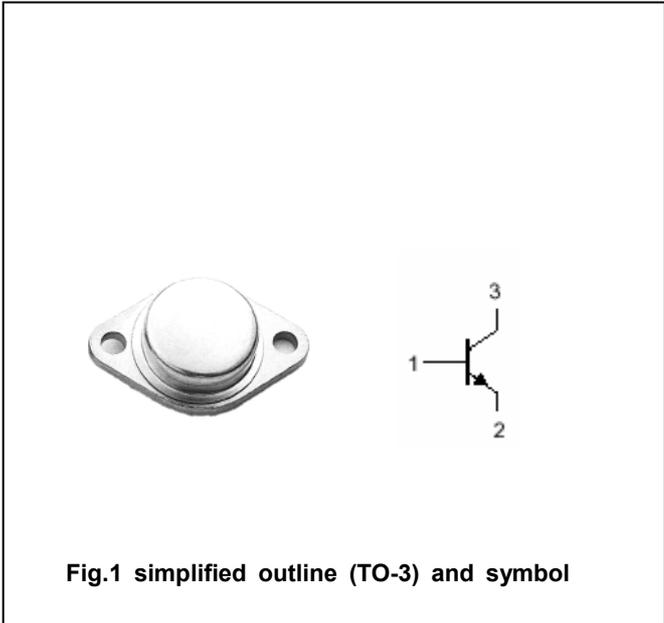


Fig.1 simplified outline (TO-3) and symbol

**MAXIMUM RATINGS(Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	300	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	225	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	6	V
I <sub>C</sub>	Collector current		5	A
I <sub>B</sub>	Base current		2	A
P <sub>T</sub>	Total power dissipation	T <sub>c</sub> =25°C	100	W
T <sub>j</sub>	Junction temperature		200	°C
T <sub>stg</sub>	Storage temperature		-65~200	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal resistance from junction to case	1.75	°C/W

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =0.2A ; I <sub>B</sub> =0	225			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =20mA ; I <sub>C</sub> =0	6			V
V <sub>CEsat-1</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =2A ; I <sub>B</sub> =0.25A			2.5	V
V <sub>CEsat-2</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4.5A ; I <sub>B</sub> =1.125A			5.0	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =2A ; V <sub>CE</sub> =10V			3.0	V
I <sub>CEV</sub>	Collector cut-off current	V <sub>CE</sub> =300V ; V <sub>BE</sub> =-1.5V T <sub>C</sub> =150°C			4.0 5.0	mA
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> =200V ; I <sub>B</sub> =0			5.0	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V ; I <sub>C</sub> =0			5.0	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =0.4A ; V <sub>CE</sub> =10V	20		80	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =2A ; V <sub>CE</sub> =10V				
h <sub>FE-3</sub>	DC current gain	I <sub>C</sub> =4.5A ; V <sub>CE</sub> =10V	5			
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =10V ; f=1MHz			250	pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.2A ; V <sub>CE</sub> =10V	2			MHz

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PACKAGE OUTLINE

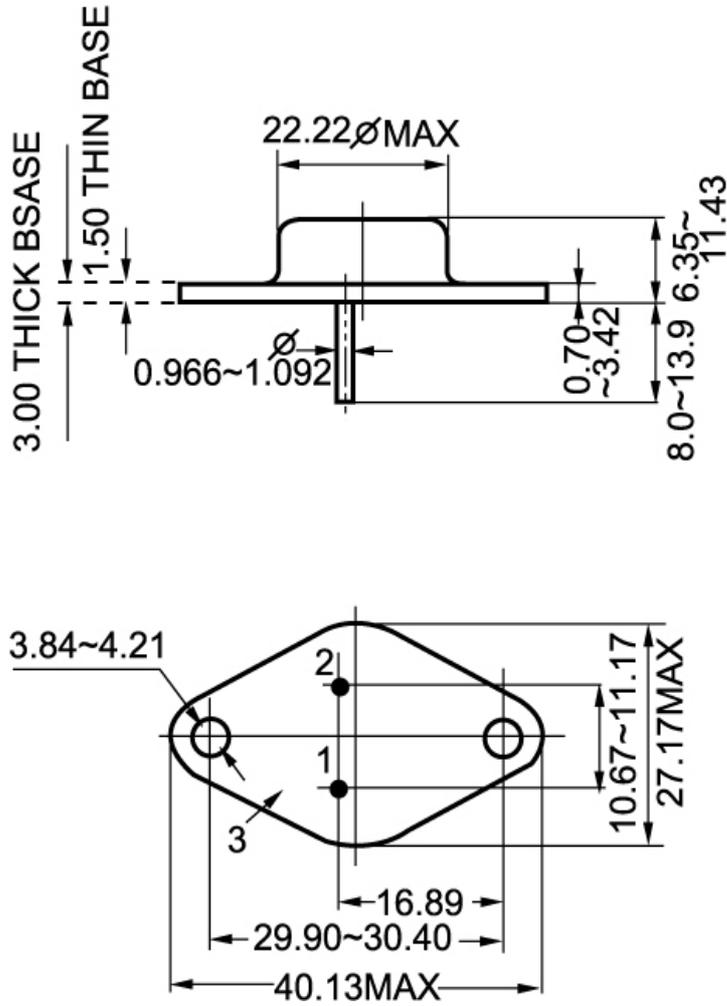


Fig.2 Outline dimensions